



50N06-F

Power MOSFET

50 Amps, 60 Volts N-CHANNEL POWER MOSFET

DESCRIPTION

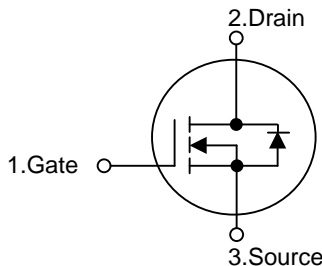
The UTC 50N06-F is three-terminal silicon device with current conduction capability of about 50A, fast switching speed. Low on-state resistance, breakdown voltage rating of 60V, and max threshold voltages of 4 volt.

It is mainly suitable electronic ballast, and low power switching mode power appliances.

FEATURES

- * $R_{DS(ON)} \leq 23 \text{ m}\Omega$ @ $V_{GS}=10V, I_D=25A$
- * Fast switching capability
- * 100% avalanche energy specified
- * Improved dv/dt capability

SYMBOL

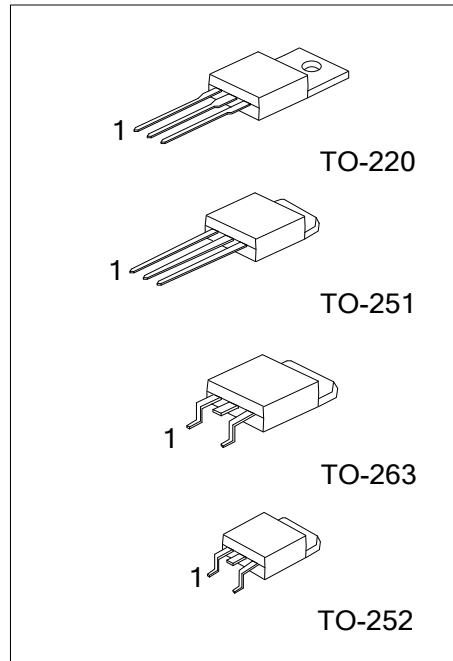


ORDERING INFORMATION

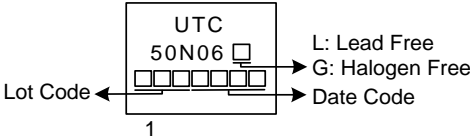
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
50N06L-TA3-T	50N06G-TA3-T	TO-220	G	D	S	Tube
50N06L-TM3-T	50N06G-TM3-T	TO-251	G	D	S	Tube
50N06L-TN3-R	50N06G-TN3-R	TO-252	G	D	S	Tape Reel
50N06L-TQ2-T	50N06G-TQ2-T	TO-263	G	D	S	Tube
50N06L-TQ2-R	50N06G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>50N06G-TA3-T</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TM3: TO-251, TN3: TO-252 TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	$T_C = 25^\circ\text{C}$	I_D	50	A
	$T_C = 100^\circ\text{C}$		35	A
Pulsed Drain Current (Note 2)		I_{DM}	200	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	480	mJ
	Repetitive (Note 2)	E_{AR}	13	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	7	V/ns
Power Dissipation ($T_C=25^\circ\text{C}$)	TO-220/TO-263	P_D	120	W
	TO-251/TO-252		46	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operation and Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by T_J

3. $L=0.38\text{mH}$, $I_{AS}=50\text{A}$, $V_{DD}=25\text{V}$, $R_G=20\Omega$, Starting $T_J=25^\circ\text{C}$

4. $I_{SD} \leq 50\text{A}$, $di/dt \leq 300\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-263	θ_{JA}	62	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		100	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-263	θ_{JC}	1.24	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		2.7 (Note)	$^\circ\text{C}/\text{W}$

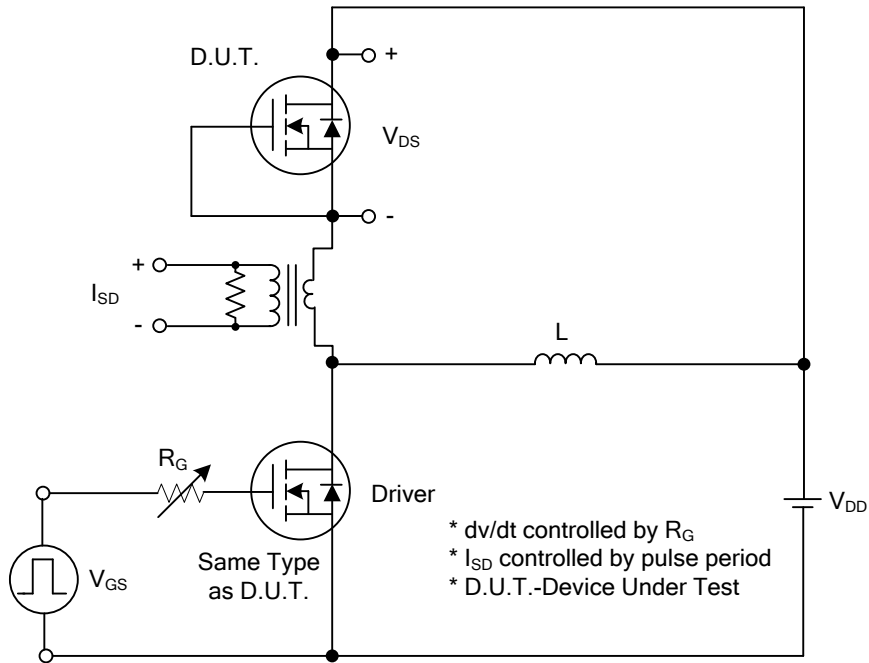
Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

■ **ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

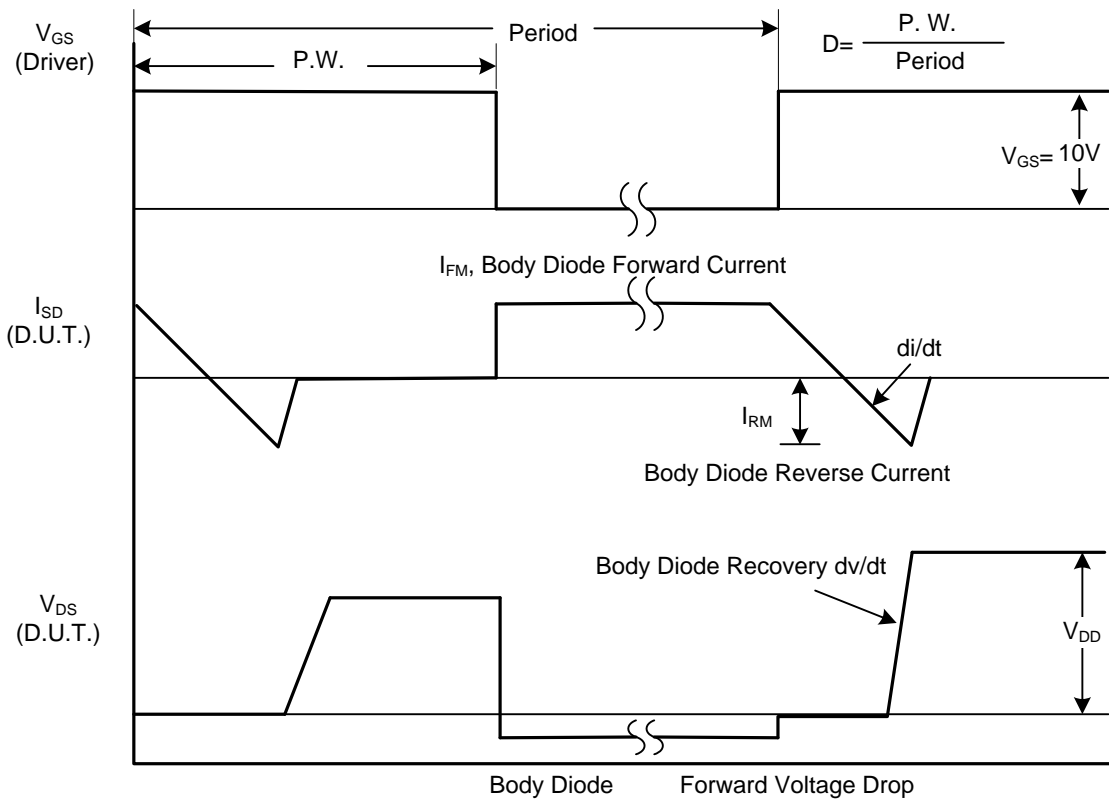
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$		100	nA
	Reverse		$V_{GS}=-20V, V_{DS}=0V$		-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, Referenced to 25°C		0.07		$V/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=25A$		18	23	$m\Omega$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$		900	1220	pF
Output Capacitance	C_{OSS}			430	550	pF
Reverse Transfer Capacitance	C_{RSS}			80	100	pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q_G	$V_{DS}=50V, V_{GS}=10V, I_D=1.3A$ (Note 1, 2)		60	80	nC
Gate-Source Charge	Q_{GS}			9		nC
Gate-Drain Charge	Q_{GD}			20		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=30V, I_D=0.5A, R_G=25\Omega$ (Note 1, 2)		60	80	ns
Turn-On Rise Time	t_R			180	220	ns
Turn-Off Delay Time	$t_{D(OFF)}$			300	350	ns
Turn-Off Fall Time	t_F			200	250	ns
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				50	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				200	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=50A, V_{GS}=0V$			1.5	V
Reverse Recovery Time	t_{rr}	$I_S=50A, V_{GS}=0V,$ $di/dt=100A/\mu s$		54		ns
Reverse Recovery Charge	Q_{rr}				81	

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
 2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

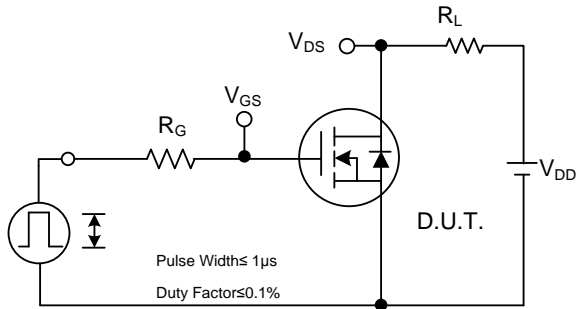


Peak Diode Recovery dv/dt Test Circuit

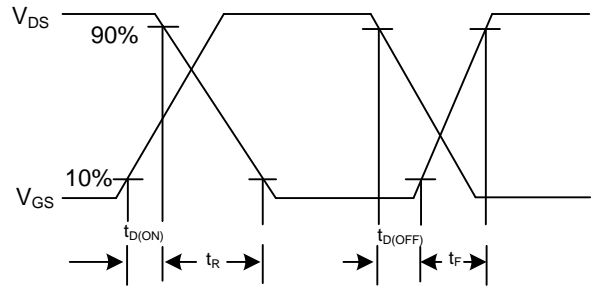


Peak Diode Recovery dv/dt Waveforms

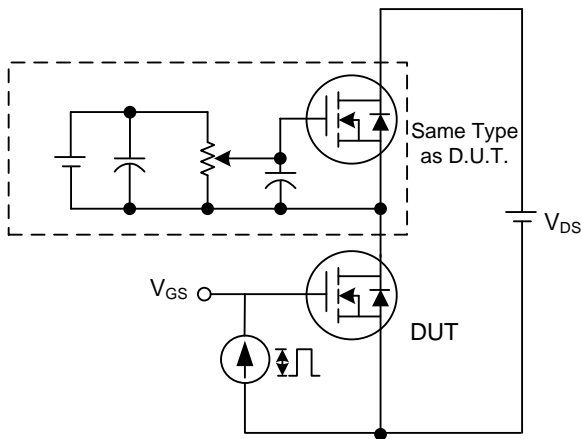
TEST CIRCUITS AND WAVEFORMS



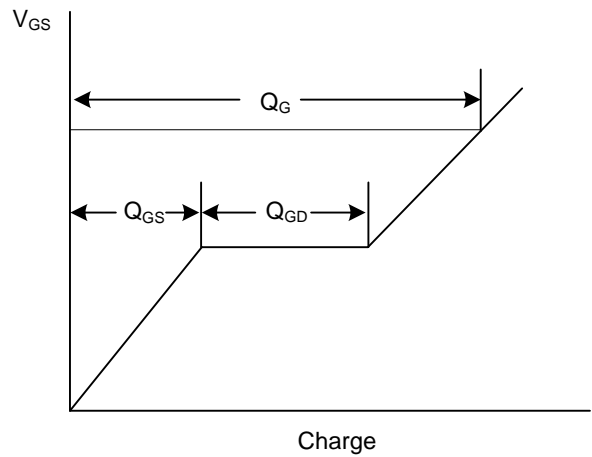
Switching Test Circuit



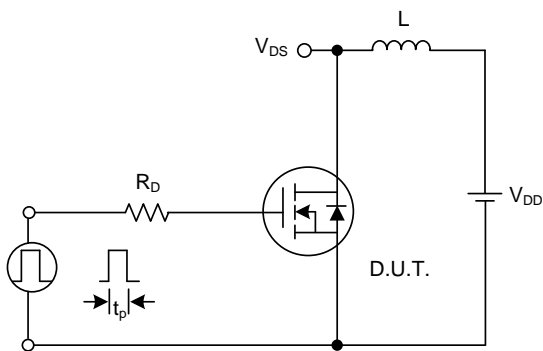
Switching Waveforms



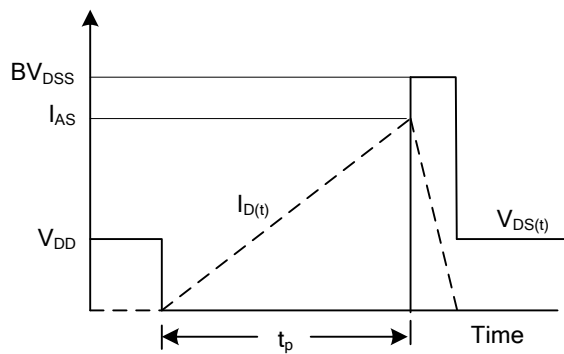
Gate Charge Test Circuit



Gate Charge Waveform

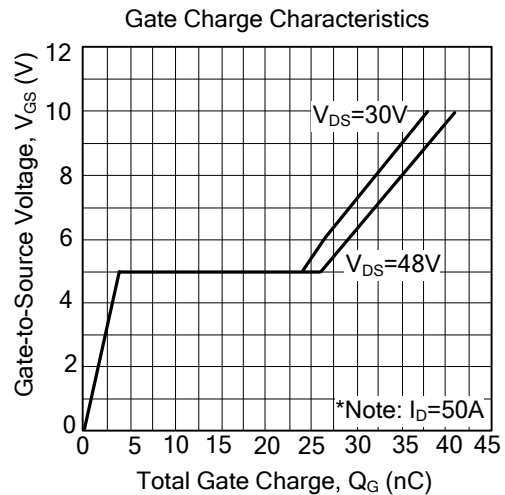
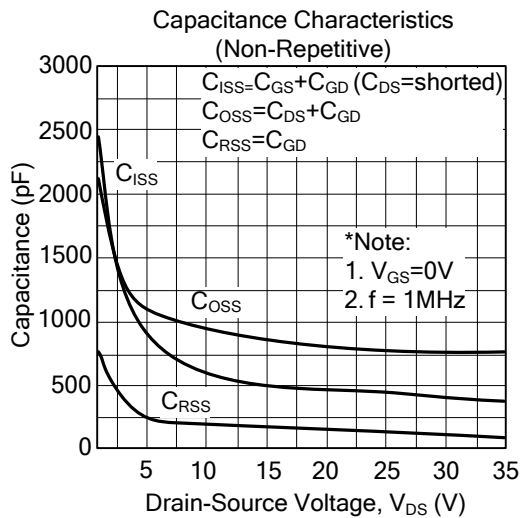
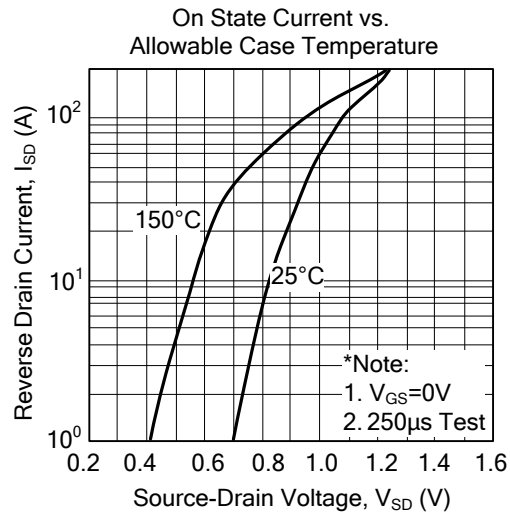
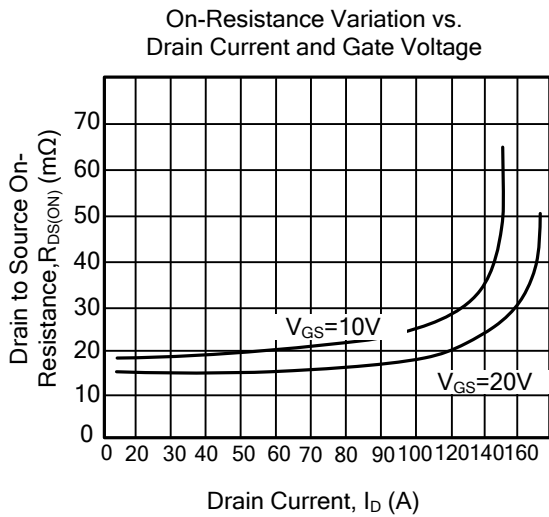
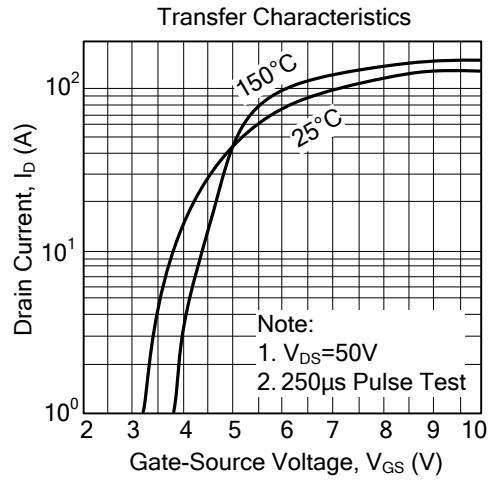
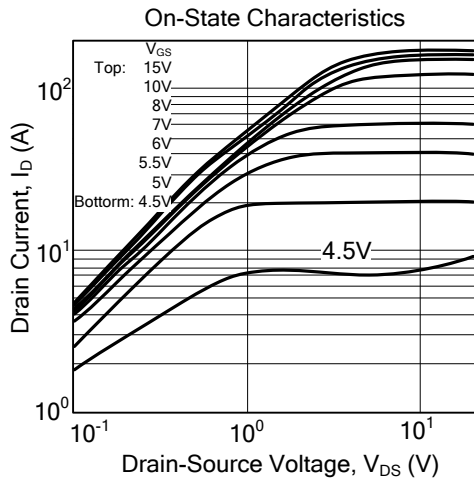


Unclamped Inductive Switching Test Circuit

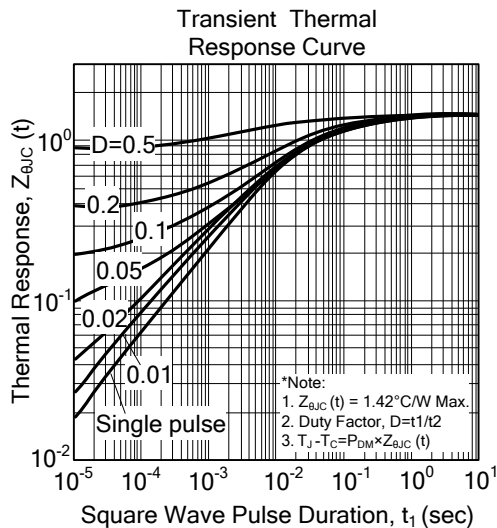
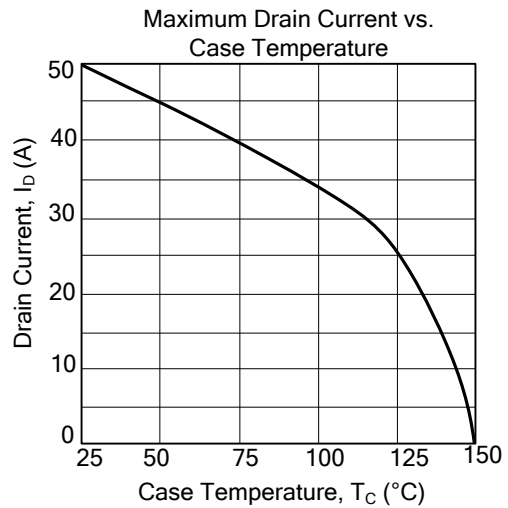
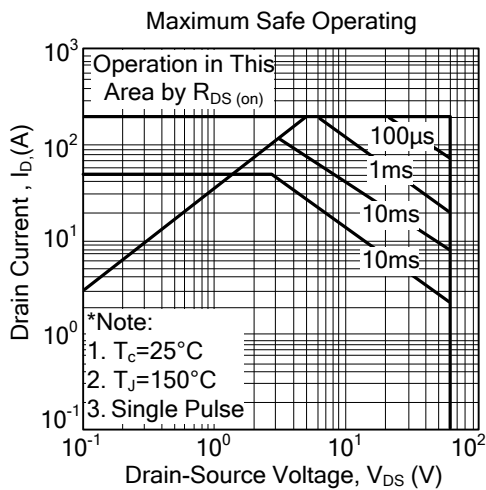
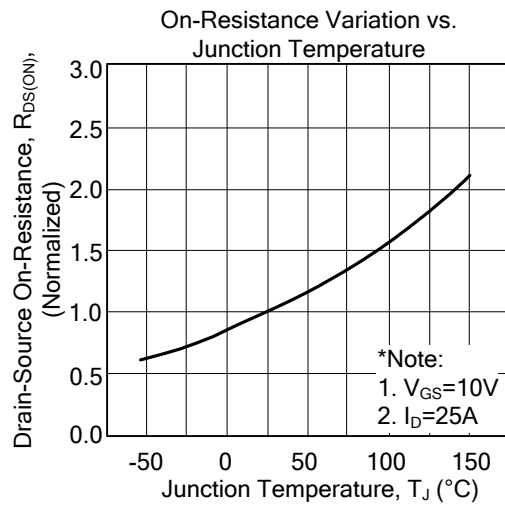
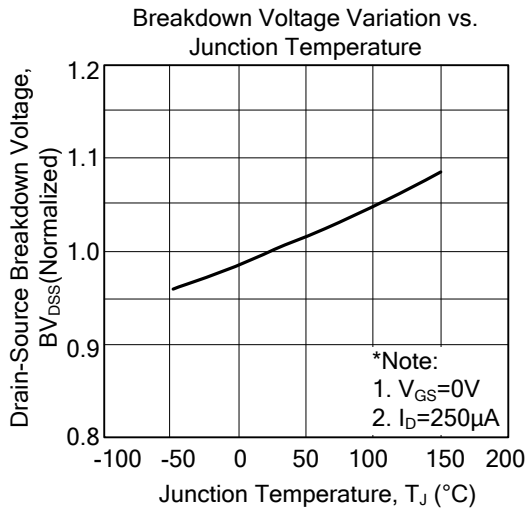


Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



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